

2SB1490

Silicon PNP epitaxial planar type Darlington

For power amplification

Complementary to 2SD2250

Features

- Optimum for 80W HiFi output
- High forward current transfer ratio h_{FE}
- Low collector to emitter saturation voltage $V_{CE(sat)} < -2.5V$

Absolute Maximum Ratings ($T_C=25^\circ C$)

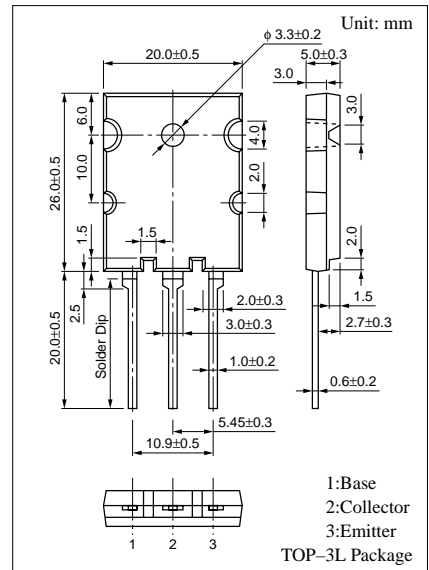
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-160	V
Collector to emitter voltage	V_{CEO}	-140	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-12	A
Collector current	I_C	-7	A
Collector power dissipation	P_C	$T_C=25^\circ C$	90
		$T_a=25^\circ C$	3.5
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics ($T_C=25^\circ C$)

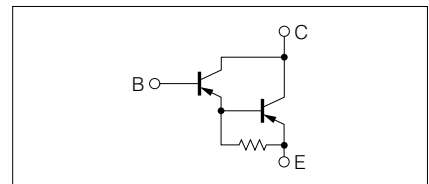
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -160V, I_E = 0$			-100	μA
	I_{CEO}	$V_{CE} = -140V, I_B = 0$			-100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	μA
Collector to emitter voltage	V_{CEO}	$I_C = -30mA, I_B = 0$	140			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = -5V, I_C = -1A$	2000			
	h_{FE2}^*	$V_{CE} = -5V, I_C = -6A$	5000		30000	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -6A, I_B = -6mA$			-2.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -6A, I_B = -6mA$			-3.0	
Transition frequency	f_T	$V_{CE} = -10V, I_C = -0.5A, f = 1MHz$		20		MHz
Turn-on time	t_{on}	$I_C = -6A, I_{B1} = -6mA, I_{B2} = 6mA,$ $V_{CC} = -50V$		1.0		μs
Storage time	t_{stg}			1.5		μs
Fall time	t_f			1.2		μs

* h_{FE2} Rank classification

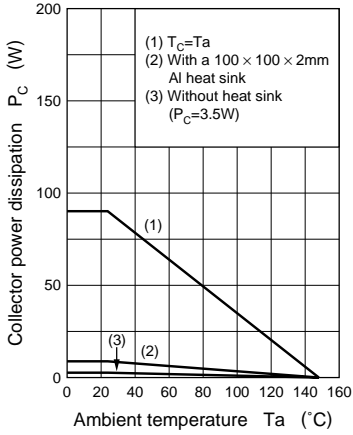
Rank	Q	P
h_{FE2}	5000 to 15000	8000 to 30000



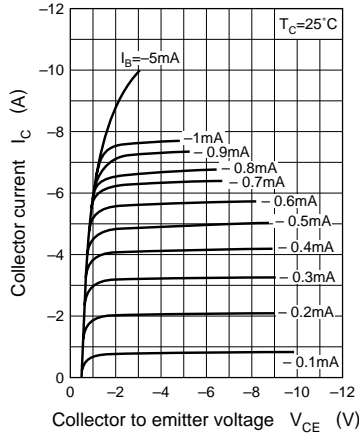
Internal Connection



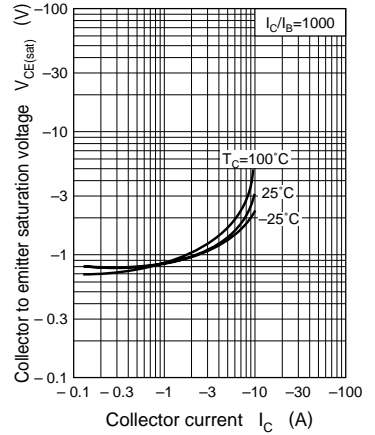
$P_C - T_a$



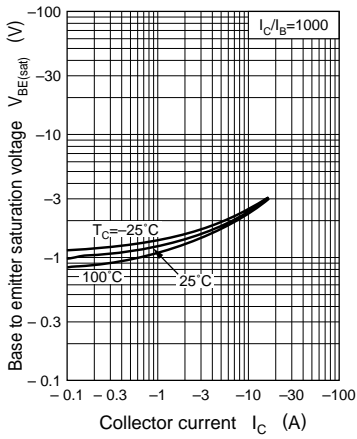
$I_C - V_{CE}$



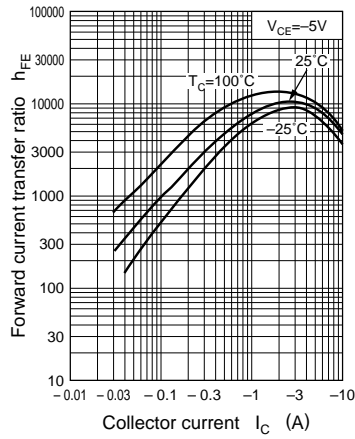
$V_{CE(sat)} - I_C$



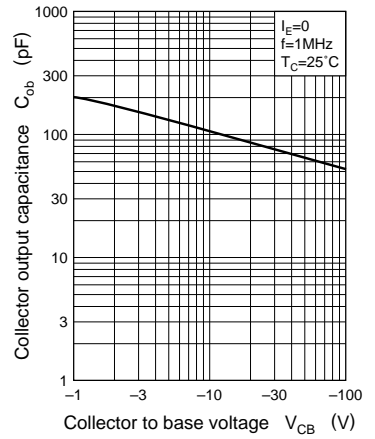
$V_{BE(sat)} - I_C$



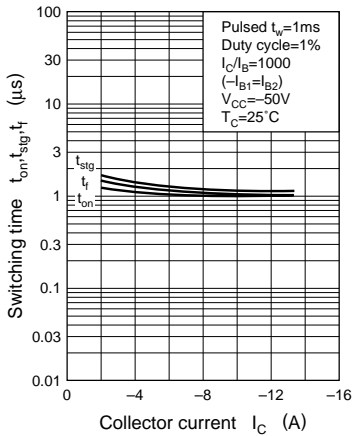
$h_{FE} - I_C$



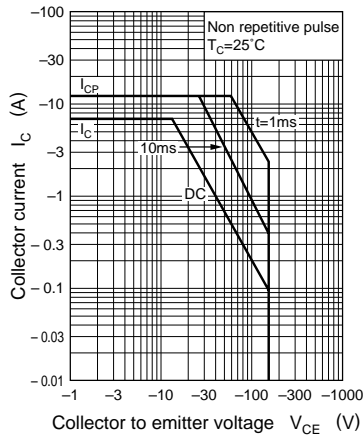
$C_{ob} - V_{CB}$



$t_{on}, t_{stg}, t_f - I_C$



Area of safe operation (ASO)



$$R_{th(t)} - t$$

